

FIG.1A

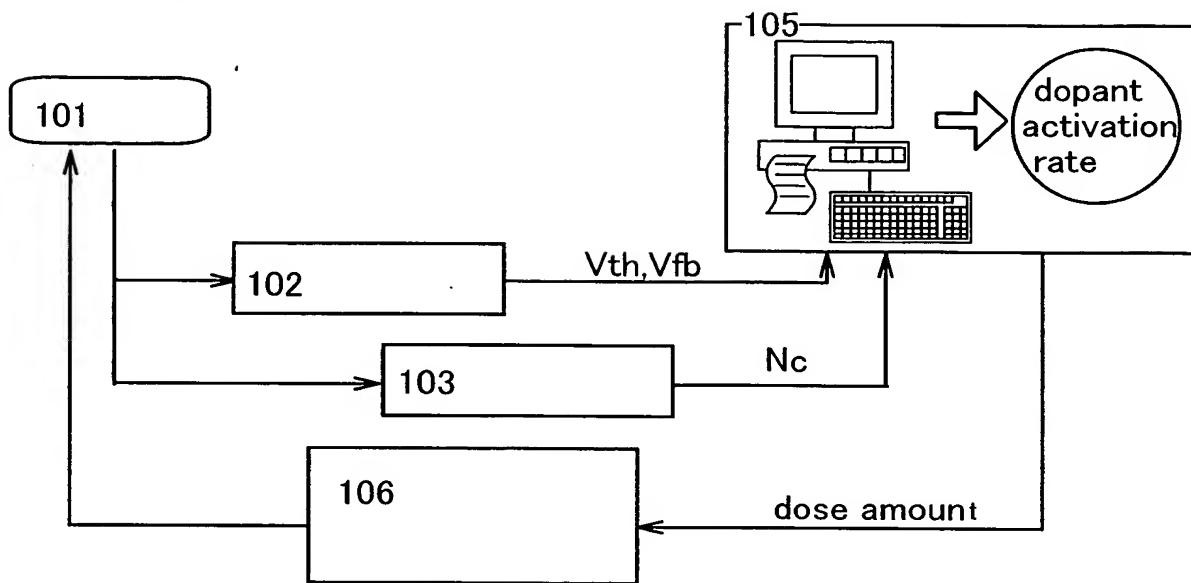


FIG.1B

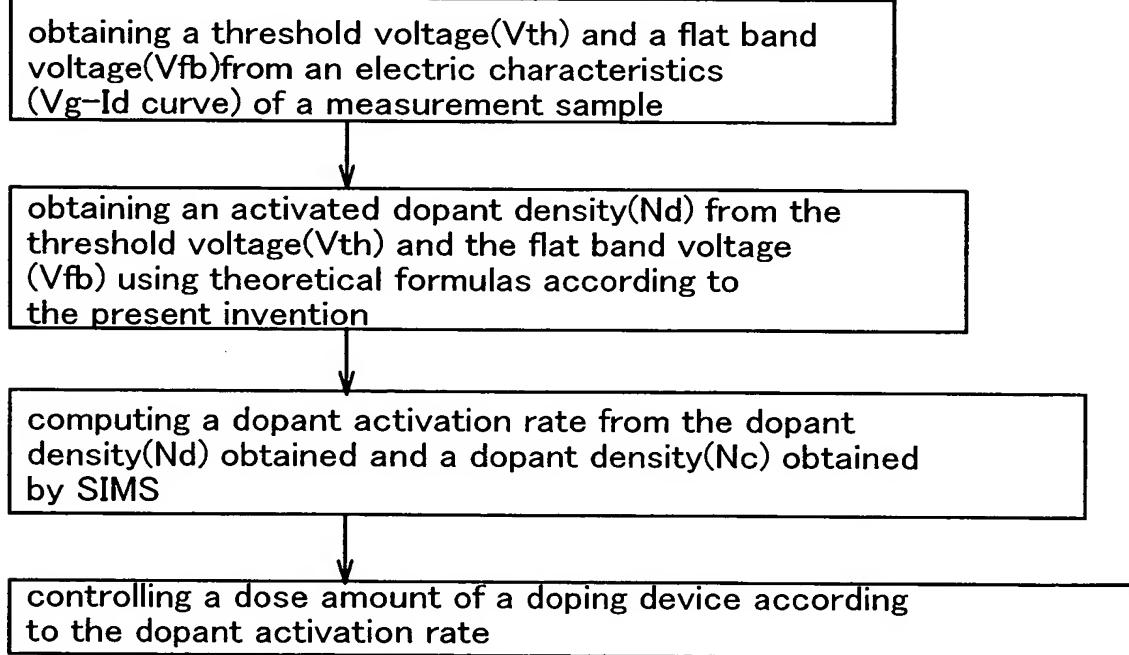


FIG.2A

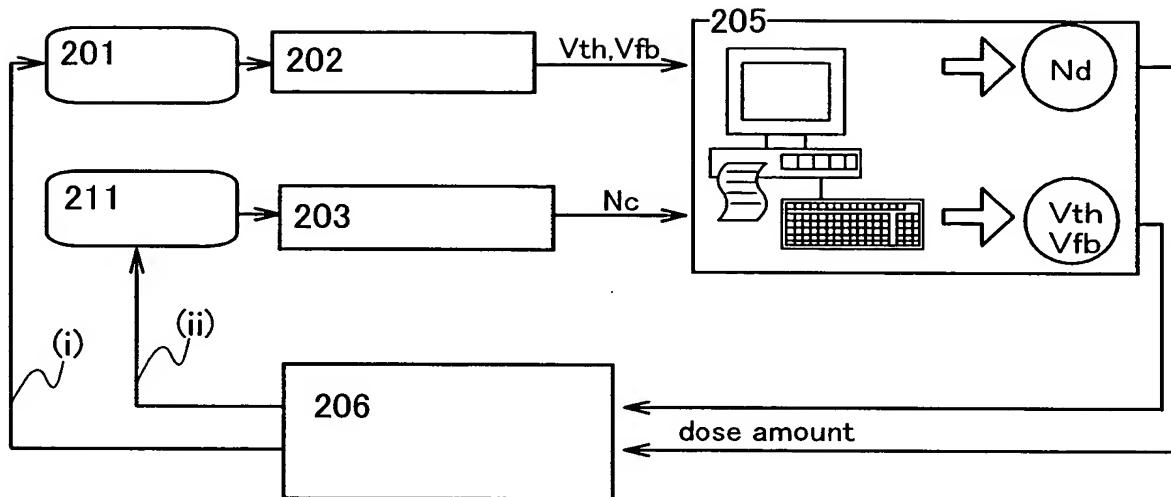


FIG.2B

(i)

obtaining a threshold voltage(V_{th}) and a flat band voltage(V_{fb}) from an electric characteristics (V_g - I_d curve) of a measurement sample



comparing a dopant activation rate data obtained by theoretical formulas according to the invention and the threshold voltage(V_{th}) and the flat band voltage(V_{fb})



obtaining a dopant density(N_d)



controlling a dose amount of a doping device according to the dopant density

(ii)

obtaining a dopant density(N_c) by SIMS analysis of a measurement sample



comparing a dopant activation rate data obtained by theoretical formulas according to the invention and the dopant density(N_c)



obtaining a threshold voltage(V_{th}) and a flat band voltage(V_{fb})



controlling a dose amount of a doping device according to the threshold voltage and the flat band voltage

FIG.3A

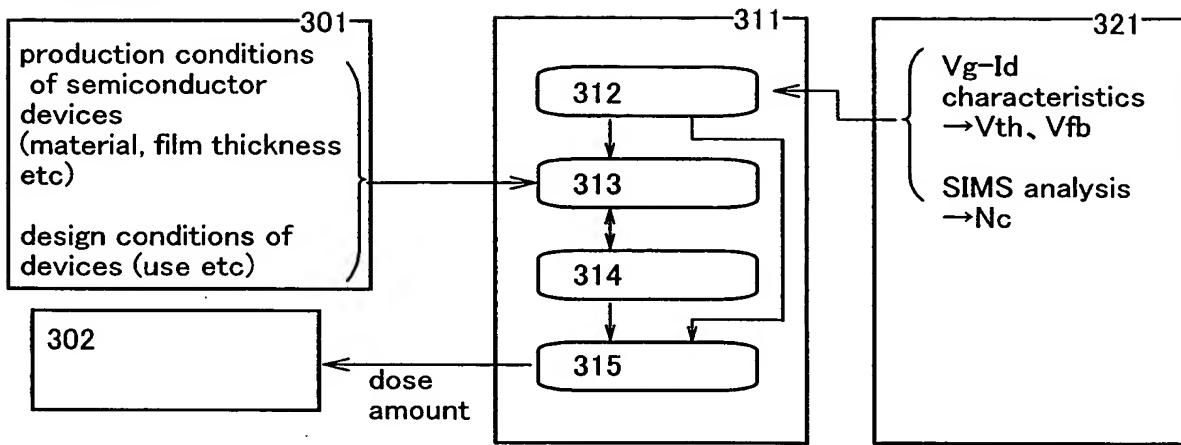
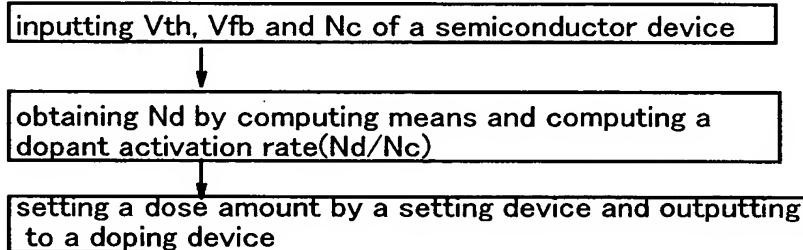


FIG.3B

(i)



(ii)

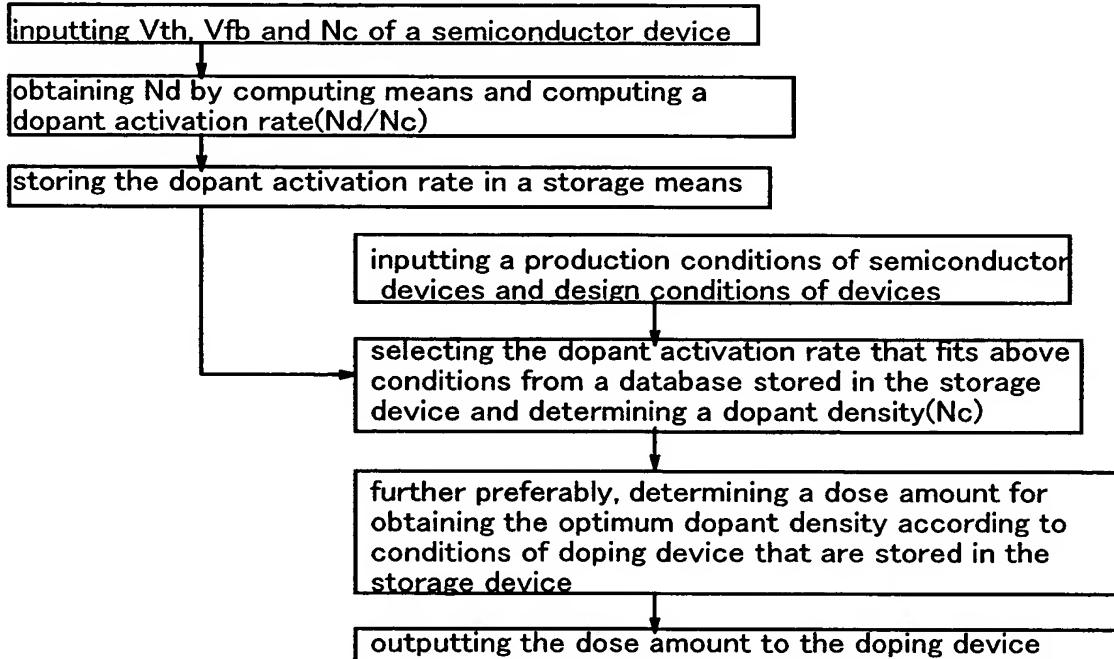
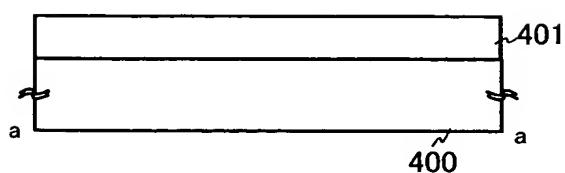
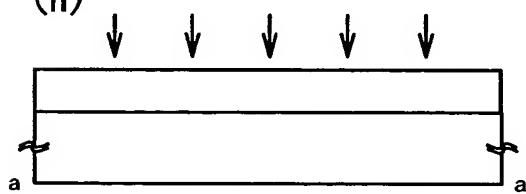


FIG.4A

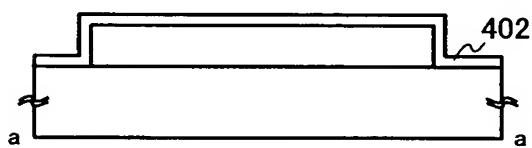
(i)



(ii)



(iii)



(iv)

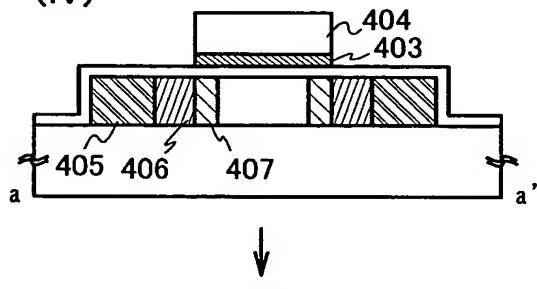
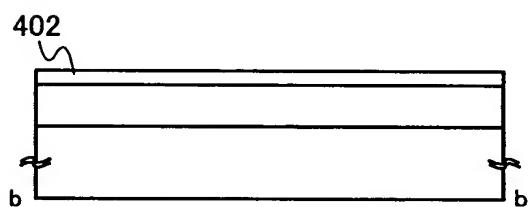
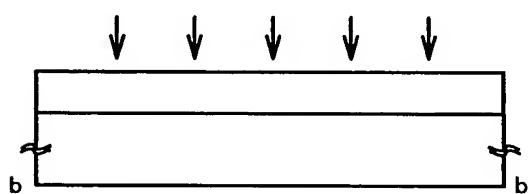
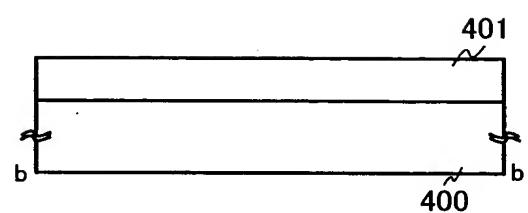


FIG.4B



↓
complete

↓
complete

FIG.5

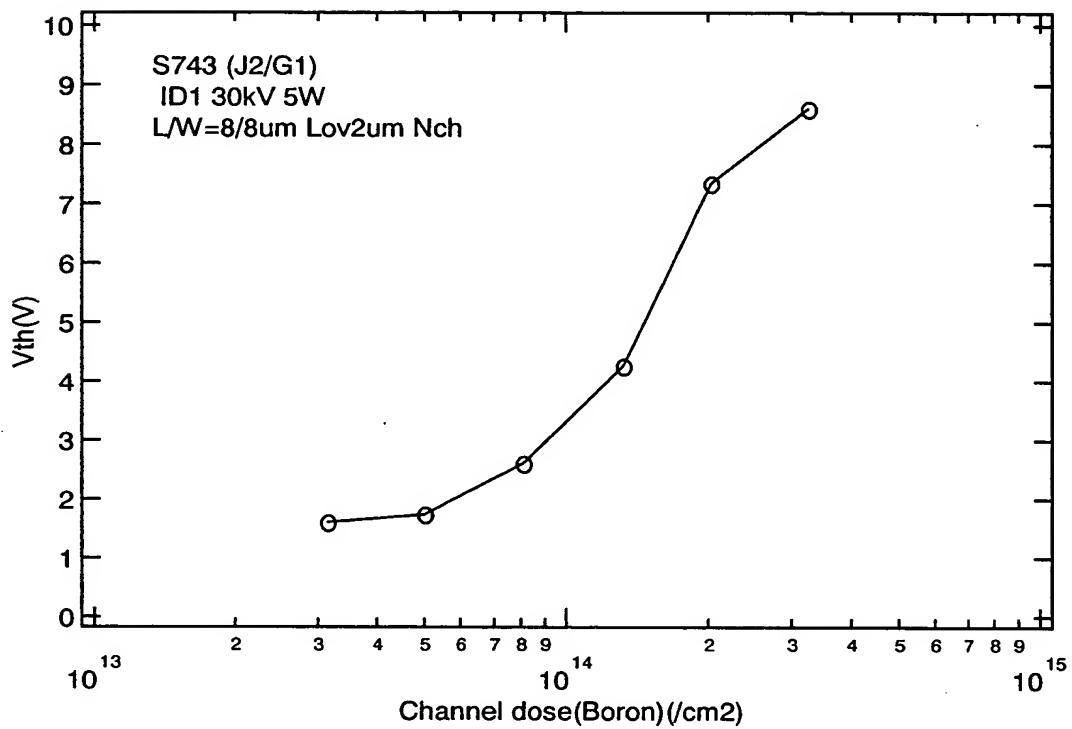


FIG.6

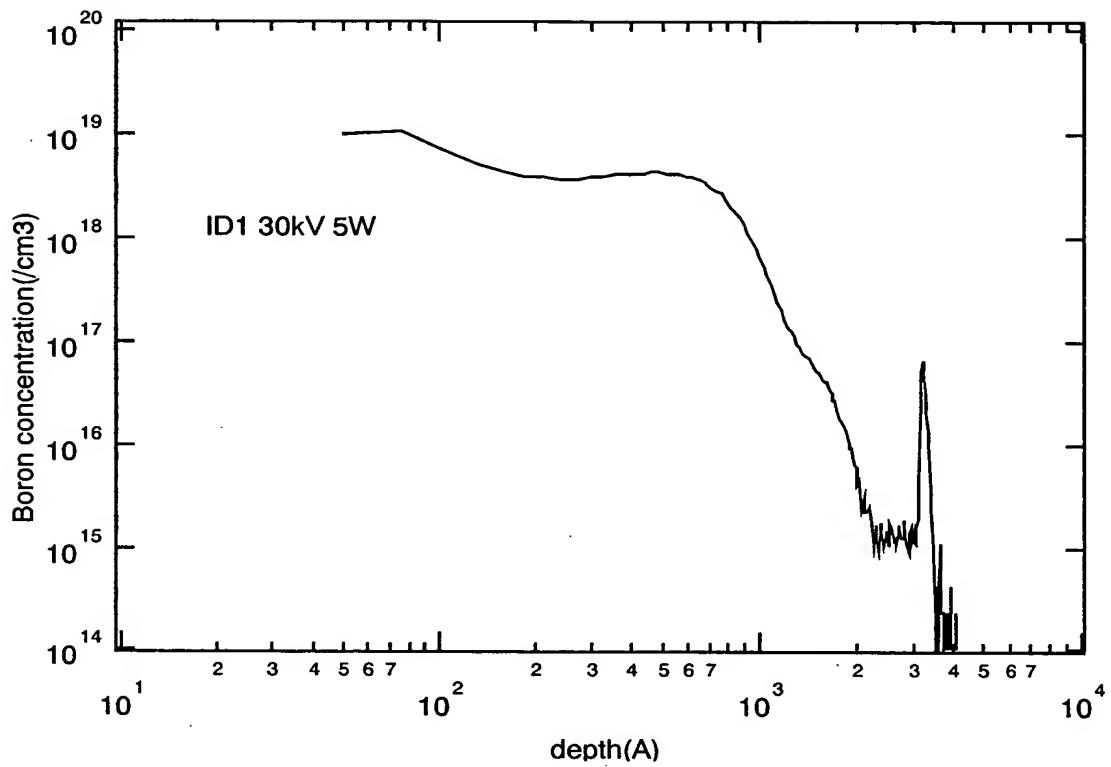


FIG.7

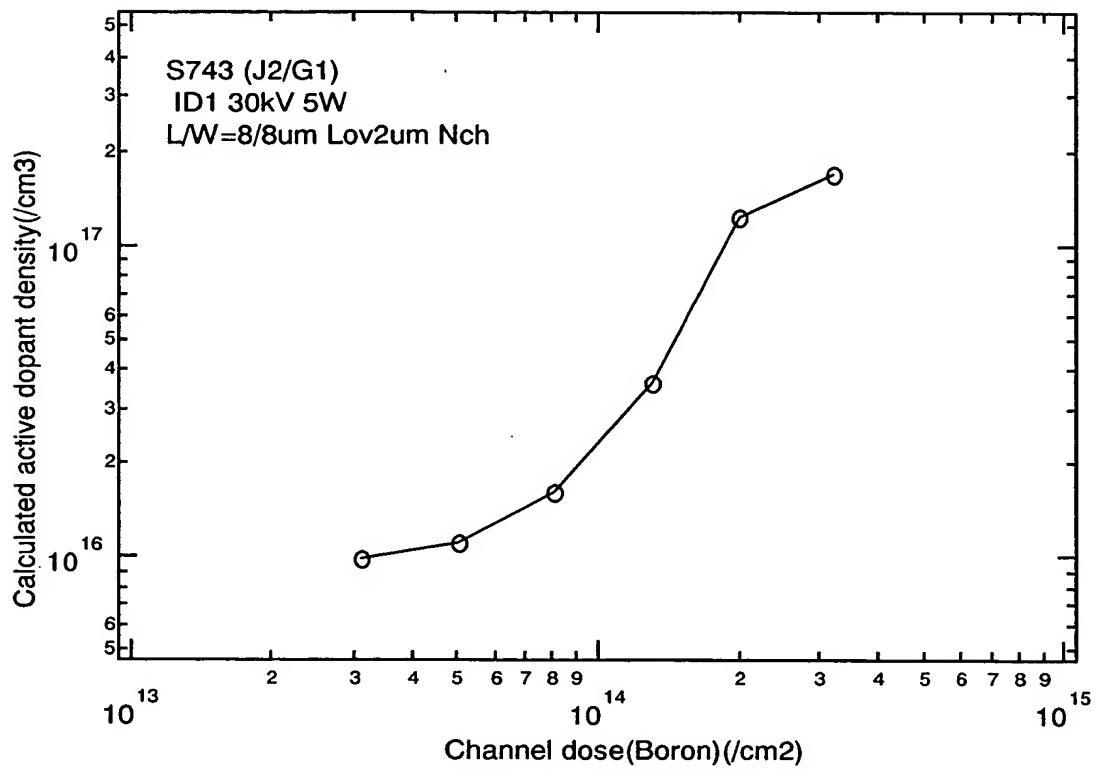


FIG.8

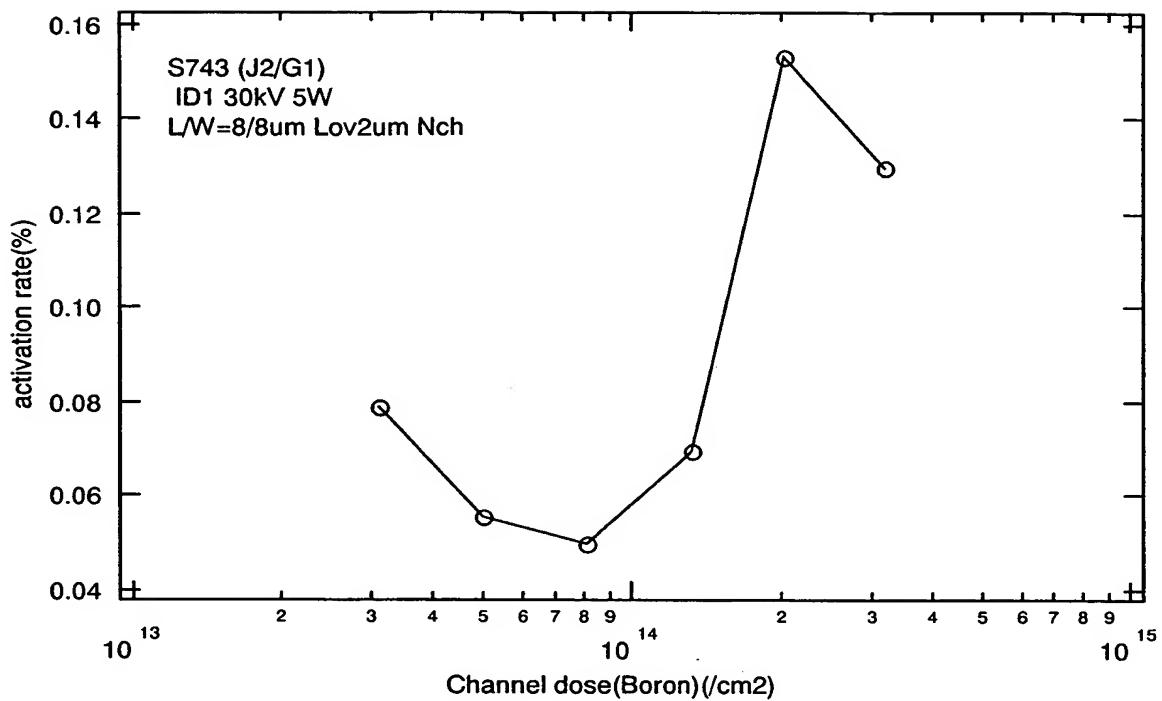
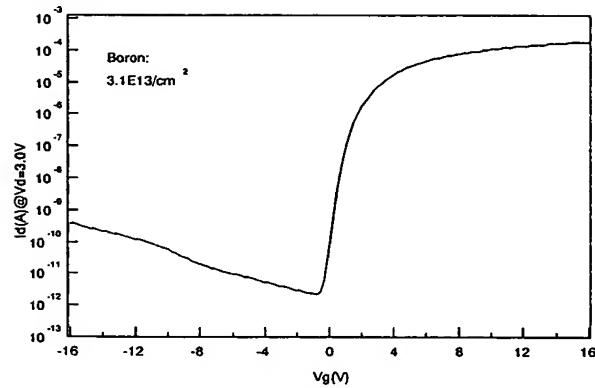
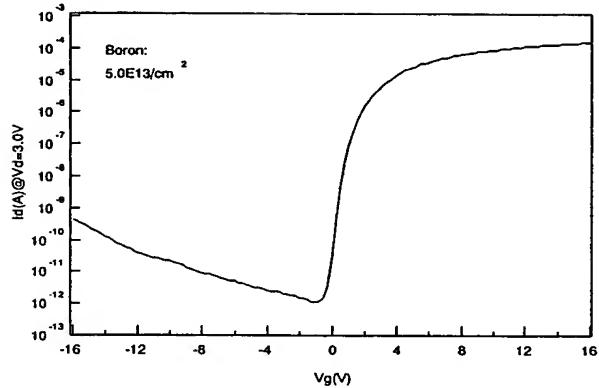


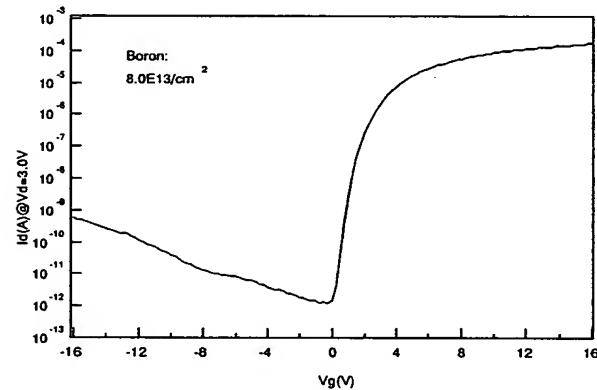
FIG.9
sample 1



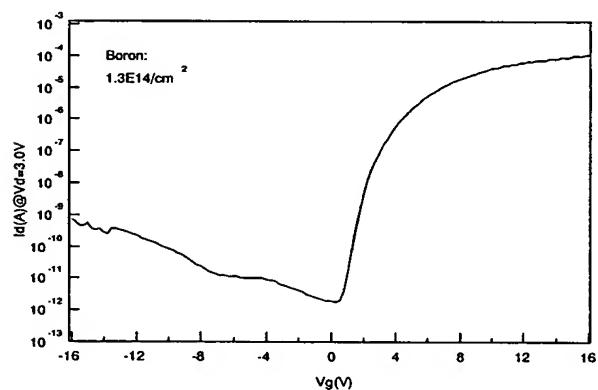
sample 2



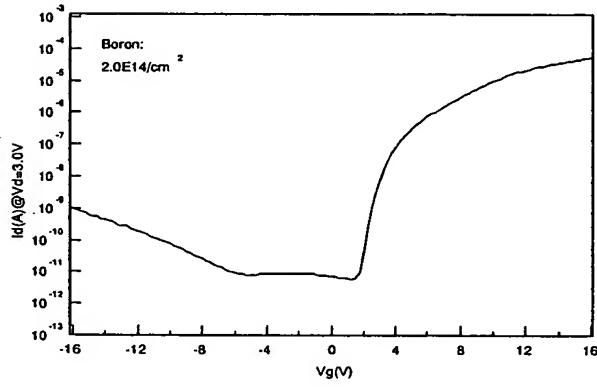
sample 3



sample 4



sample 5



sample 6

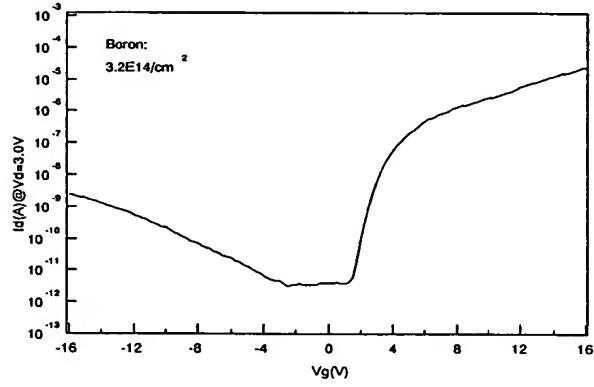


FIG.10

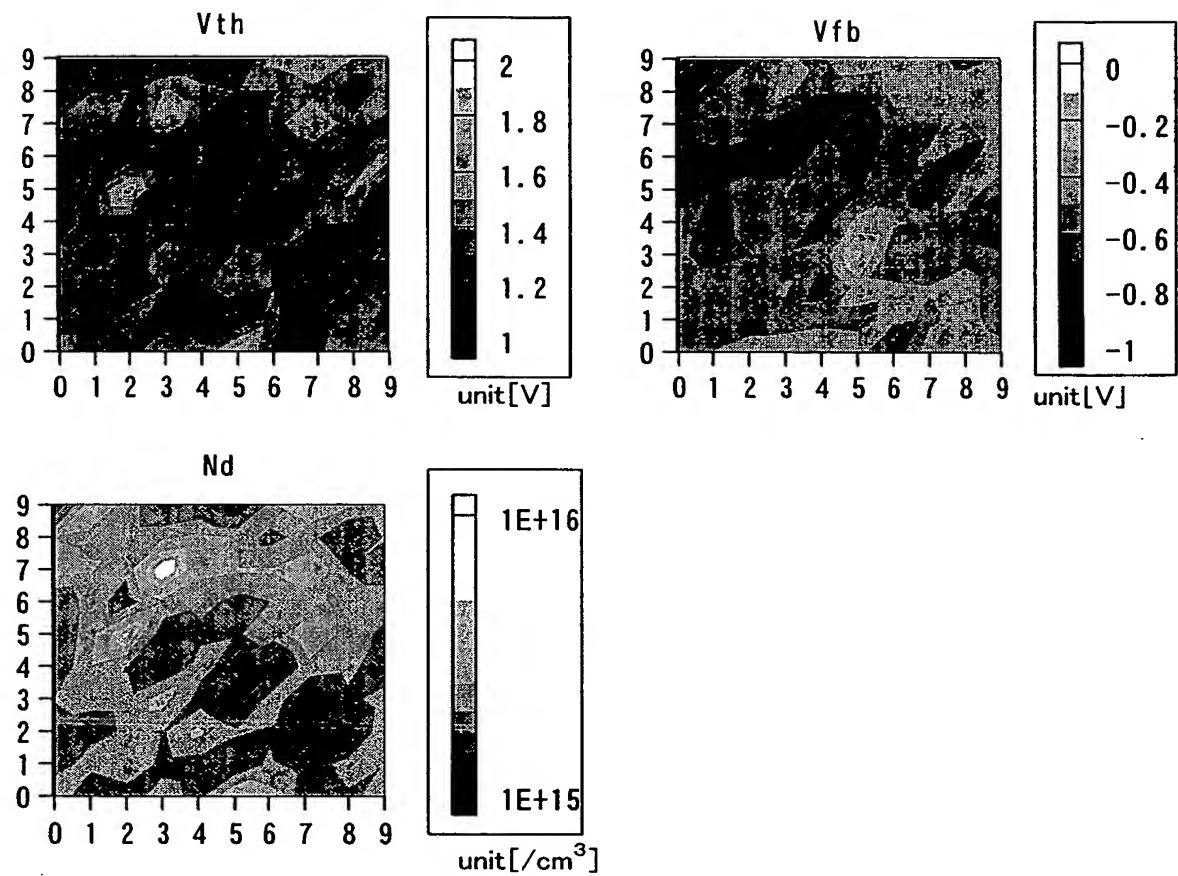


FIG.11

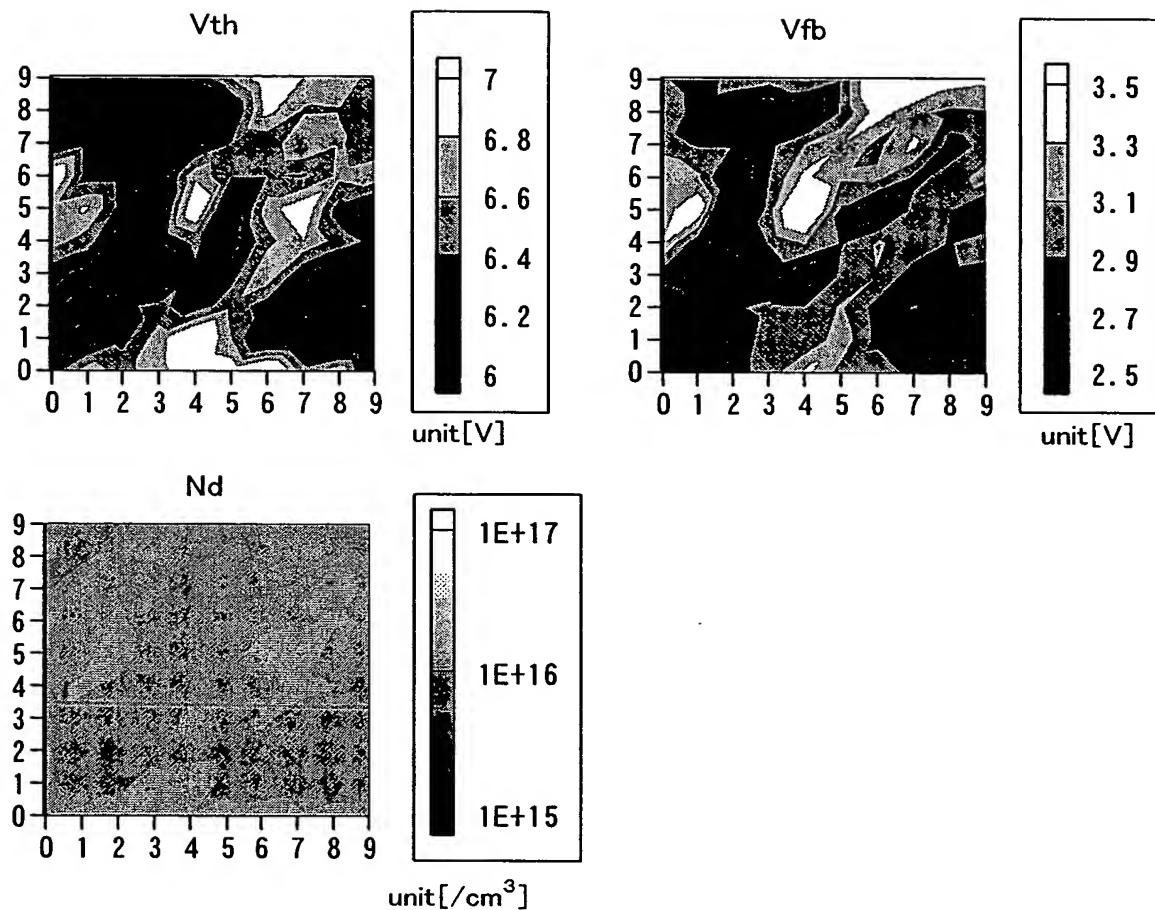


FIG.12

